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11. (Amended) The semiconductor structure of claim 10, wherein the surfactant material comprises at least one of Al, In, and Ga.

13. (Amended) The semiconductor structure of claim 12, wherein the capping layer is formed by exposing the surfactant material to a cap-inducing material.

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14. (Amended) The semiconductor structure of claim 13, wherein the cap-inducing material comprises at least one of As, P, Sb, and N.

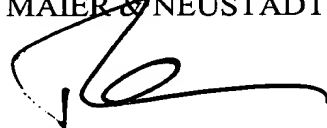
15. (Amended) The semiconductor structure of claim 12, wherein the surfactant comprises Al, and the capping layer comprises Al₂Sr.--

REMARKS

The above amendment to the claims corrects the dependency of Claims 7-15, as required.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND,
MAIER & NEUSTADT, P.C.



Richard L. Treanor
Attorney of Record
Registration No.: 36,379



22850
Telephone: (703) 413-3000
Facsimile (703) 413-2220

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IN THE CLAIMS

Please amend Claim 7, 8, 10, 11, 13, 14, and 15 as follows.

--7. (Amended) The semiconductor structure of claim [7] 6, wherein the template layer is formed of material selected from the group comprising Ti-As, Sr-O-As, Sr-Ga-O, Ti-O-As, or Sr-Al-O.

8. (Amended) The semiconductor structure of claim [7] 6, wherein the template layer comprises a Zintl-type phase material.

10. (Amended) The semiconductor structure of claim [7] 6, wherein the template layer comprises a surfactant material.

11. (Amended) The semiconductor structure of claim [11] 10, wherein the surfactant material comprises at least one of Al, In, and Ga.

13. (Amended) The semiconductor structure of claim [13] 12, wherein the capping layer is formed by exposing the surfactant material to a cap-inducing material.

14. (Amended) The semiconductor structure of claim [14] 13, wherein the cap-inducing material comprises at least one of As, P, Sb, and N.

15. (Amended) The semiconductor structure of claim [13] 12, wherein the surfactant comprises Al, and the capping layer comprises Al₂Sr.--